Subject Index

Α

Acceptor compensator, 313 Admittance, metal oxide semiconductor (MOS), 381 Aging of silicon, 313 AlGaAs qualification techniques, 628 Aluminum etching, 250 Amorphization, 108 Amorphous silicon, 241 Arsenic, 521 ASTM Standards, 15 F 121: 367 F 123-83: 372 F 523: 282 F 723: 474 Atomic distributions, 480 profiling, 535 Auger Electron Spectroscopy, 119, 178, 628 Autodoping, 21, 33 Automated guided vehicles (AGVs), 653 Automated production processes automatic resistivity tester (ART), 602 computer-aided process optimization, 246 computer-assisted manufacturing (CAM), 653 computer-integrated manufacturing (CIM), 662 equipment reliability, 673 material handling, 653 particle and material control system, 414 wafer fabrication automation, 653 Automatic resistivity tester (ART), 602

в

Backscatter, Rutherford, 119, 688 Backsurface damage, 324 Barrel reactor, 79 Beryllium implants, 628 Bonding structure, 173 Boron, 204, 521, 573 BPSG, 615 Buried layers, 21

С

C₂ClF₅, 204 Cārbon, in silicon, 365, 683 Carrier distributions, 480, 502, 558 Channel mobility, 21 Charged particle activation analysis, 365 Chemical vapor deposition (CVD) bonding structure, 173 cold wall, 35 low pressure, 173 low temperature, 24, 43 plasma enhanced, 21, 173 reactor design, 129 thin epitaxial silicon deposition, 33 uniformity, 129 Chlorinated gases, 204 Clean room technology, 414, 423 CMOS technology epitaxial quality, 51 silicon epitaxial growth on N+ substrate, 65 Comprehensive uptime, 673 Computer-aided process optimization, 246 Computer-assisted manufacturing (CAM), 653 Computer-integrated manufacturing (CIM), 662 Conductivity, 480 Contamination carbon, 365 control, 336, 414, 423 hydrogen, 313 measurement, 119, 365 oxygen, 365 process gases, 436 reactive ion etching damage, 163 Conversion coefficient, 365

695

Correction factors, 480, 502 CV, electrochemical, 558 D Damage backsurface, 324 control, 163 displacement, 535 from reactive ion etching, 163 ingot-to-wafer processing, 297 plasma, 220 radiation, 381 Dedicated processing, 662 Defects, 281, 336, 381 Deposition uniformity, 129 Depth profiling, 453, 521 Design rules, 404 Device sensitivity, 393 Diameter scans, 598 Dielectrics, 137, 173, 220, 336 Diffusion, doped oxide spin-on source, 95 Displacement damage, 535 Distributed software functions and system architecture, 662 Doping and dopants autodoping, 21 carrier distributions, 480, 502, 558 cross-contamination, 119 implant, 204 profiling (See Profile control and analysis) spreading resistance (See Spreading resistance measurements)

Ε

Edge profile, 204 Education for the electronics industry, 691 Electrochemical CV, 558 Emission endpoint, plasma etch, 190 Epitaxial films growth on N+ substrate, 65, 79 layers, 586, 598

quality, 51 silicon, 79, 281 surface defects, 281 Epitaxy chemical vapor deposition (CVD), 33 HCL etching, 79 layers, 586 low-temperature deposition, 24 molecular beam, 558 plasma-enhanced CVD, 21 quality, 51 silicon-on-sapphire, 33 surface defects, 281 Equipment-dependent uptime, 673 Error propagation, 393 ESCA analysis, 313 Etching aluminum, 250 anisotropy, 79 high-temperature vapor, 79 in situ HCl, 79 metal dry, 250 palladium, 273 plasma, 220 plasma etch emission endpoint, 190 rate, 79 reactive ion, 220, 250 uniformity, 190 Exposure ambient, 257

F

Fabrication automation (See Automated production processes) Factory communications, 653 Films (See also Epitaxial films) palladium, 266 silicon dielectric, 173 silicon dioxide breakdown, 336 Filtration, 436 Finite element method, 480 Fluorinated gases, 204 Four-point probe, 586 Fourier transform infrared spectroscopy (FT-IR), 353 Fracture, ingot, 297

Free carrier absorption, 353 Freon 115, 204

G

Gallium arsenide, 220, 628, 643 Gases, process, 436 Gettering effects on epitaxial quality, 51 impurities, 324, 336 internal, 8, 65 intrinsic, 51, 353, 686 Global environment, 662

Н

Haze, 79, 313 HCl etching, 79 Hydrogen analysis, 313

Ι

Implantation, 453 beryllium, 628 cross-contamination levels produced, 119 knock-on, 535 profile control of plasma-etched polysilicon, 204 Infrared absorption spectroscopy, 353, 628, 684 Ingot processing damage, 297 Insulators, 137 Integration, system, 662 Interface defects, 381 Interstitial oxygen measurements, 353 Ion beam implantation, 453 cross-contamination levels produced, 119 damage, 150 into same-conductivitytype substrates, 586 into 200-mm wafers, 598 knock-on, 535 low-dose, 586 nitridation, 150

Junction breakdown voltage, 51 depth, 573 Junction formation techniques, 95, 266 Just-in-time material delivery, 653

K

Knock-on, 535

\mathbf{L}

Laplace's equation, 480 Laser ionization mass analysis (LIMA), 324 Laser scanning, 281 Latch-up, 51 Lithography, X-ray, 257 Loading effect, 190 Logistic time, 673 Low-pressure deposition, 21 Low-temperature deposition, 21, 24

М

Manufacturing (See also Automated production processes) computer-assisted manufacturing (CAM), 653 computer-integrated manufacturing (CIM), 662 equipment reliability, 673 mechanical processing, 297 particle and material control, 414, 423 standards, 15 variability, 393 wafer fabrication automation, 653 Maps, three-dimensional (contour), 598 Materials (See also Gallium arsenide; Silicon) contamination measurements, 119

J

698 EMERGING SEMICONDUCTOR TECHNOLOGY

Materials (Continued) control, 414 defects, 54, 65, 281 Mean time between assists (MTBA), 673 Mean time between failures (MTBF), 673 Mean time to assist (MTTA), 673 Mean time to repair (MTTR), 673 Mechanical processing, 297 Metal oxide semiconductor (MOS) devices, 150, 336, 381 Microdefects, 65 Mobility, 150 Modeling process, 573 yield, 404 Molecular beam epitaxy, 558 Monte Carlo method, 190, 535

0

Optical analysis techniques, 628 Optically activated states, 381 Oxide layer analysis, 615 Oxygen, in silicon, 353, 365, 683

Ρ

Palladium silicide-silicon contacts, 266 Parametric variability, 393 Pareto analysis, 393 Particulate control, 414, 423, 436 Phosphorus, 204 Photoconductivity, transient, 241 Photoluminescence quenching, 628 Photoresists, 250 Plasma technology deposition of amorphous silicon, 241 etch emission endpoint, 190 etching, 190, 220, 423 plasma damage, 220

plasma-enhanced chemical vapor deposition, 21, 173 processes, table, 223 processing of dielectric layers, 220 profile control of etching, 204 quality control during plasma deposition, 241 reactive ion etching (RIE), 163, 220, 250 Poisson's equation, 480 Polysilicon, 204 Precipitation effects, oxygen and carbon in silicon, 683 Process simulation, 404, 573 Processing dedicated, 662 mechanical, 297 Production processes, automated, 241 Productive time, 673 Profile control and analysis dopant, 95, 573, 687 electrochemical CV, 558 impurity profiles, 521 of plasma-etched polysilicon, 204 primary kinematic knockon in SIMS, 535 sampling volume correction factors, 502 spreading resistance, 453, 480, 558 PSG deposition, 204, 615

Q

Quality control during plasma deposition, 241 using laser scanning, 281 Quenching, photoluminescence, 628

R

Radiation damage, 381 deep ultraviolet, 250

Reactive ion etching damage, 163 on gallium arsenide ICs, 220 UV radiation, effects of, 250 Reactor design and productivity, 129 Real-time shop floor control, 653 Recoil implantation, 535 Reduced pressure, 33 Reliability of manufacturing equipment, 673 Resistance sheet, 95, 598 spreading (See Spreading resistance measurements) Resistivity mapping, 586, 598 Rutherford Backscattering Spectroscopy, 119, 688

S

Sampling volume correction factors, 502 Berkowitz-Lux algorithm, 510 Local slope technique, 508 PROF algorithm, 510 Schumann-Gardner Theory, 505 Scans, diameter, 598 Scheduled time, 673 Secondary ion mass spectrometry (SIMS), 521, 535, 573, 687 Semiconductor Equipment and Materials Institute (SEMI) Standards, 16 Semiconductors business forecasts, 7 equations, 480 free carrier absorption, 353 interstitial oxygen measurements, 353 materials gallium arsenide, 220, 628, 643 silicon (See Silicon)

silicon-on-sapphire, 33 standards (See Standards) yield enhancement, 404, 423 Sensitivity, device, 393 SF₆, 204 Sheet resistivity, 95, 598, 688 Shot noise, 257 Silicon aging, 313 amorphous, 241 carbon contamination, 365, 683 contamination control, 336 damage, 297 defects, 281, 336, 381 dielectrics, 173 dioxide, 336, 381 doped oxide source diffusion, 95 electrochemical CV, 558 epitaxy chemical vapor deposition (CVD), 33 HCL etching, 79 layers, 586 low-temperature deposition, 24 molecular beam, 558 plasma-enhanced CVD, 21 quality, 51 silicon-on-sapphire, 33 surface defects, 281 gettered impurities, 324 haze generation, 313 hydrogen contamination, 313 impurity profiling and measurement, 119, 365, 521 infrared absorption, 353, 684 local oxidation of, 150 mapping, 586 moisture effects on, 313 n-type, 353 oxygen contamination, 365, 683 oxynitride, 173 p-type, 353 process control, 586 profile control of etching, 204

Silicon (Continued) reactive ion etching damage, 163 spreading resistance (See Spreading resistance measurements) X-ray fluorescence analysis, 615 SF₆, 204 Silicon-oxide interface, 381 Software functions, distributed, 662 Solar cells, 297 Source diffusion, doped oxide spin-on, 95 Spreading resistance measurements boron profile analysis, 573 carrier density calculations, 480 comparison with electrochemical CV, 558 comparison with fourpoint-probe measurements, 586 comparison with secondary ion mass spectrometry, 521 correction factors, 480, 502 incremental sheet resistance, 688 multilayer Laplace equation analysis, 480 overview, 453 shallow xenon implantation, 108 Sputtering, 137, 535 Standard mechanical interface (SMIF), 414 Standards applications, 15 ASTM F 121: 367 ASTM F 123-83: 372 ASTM F 523: 282 ASTM F 723: 474 development organizations, 15 international cooperation in, 15 Standby time, 673

Statistical modeling, 393
SUPREM computer modeling
 program, 526, 573,
 689
Surface
 analysis techniques, 628
 cleaning, 24, 288
 defects, 281
 roughness, 150
System
 architecture,
 distributed, 662
 integration, 662
 moments, generation of,
 393

т

Thin films, 137 Transient photoconductivity, 241 Transistors, MOS, 150, 336, 381 Transition width, 33 Trend analysis, 598 TRIM Monte Carlo code, 538

U

Ultraviolet radiation, 250 Undercut, 204 Uniformity of plasma etch, 190 Unscheduled time, 673 Uptime comprehensive, 673 equipment dependent, 673

V

 Ŵ

Wafers cracks, 297 inspection, 281 large diameter, 598 processing, 598 thin-layer analysis by Xray fluorescence, 615 uniformity, 598 zone engineering, 8 Х

X-ray fluorescence analysis, 615 lithography, 257 resist, 257 Xenon ionic implantation, 108

Y

Yield analysis and enhancement, 404, 423